BCW66GLT1G, SBCW66GLT1G

General Purpose Transistor

NPN Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	45	Vdc
Collector - Base Voltage	V _{CBO}	75	Vdc
Emitter – Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	I _C	800	mAdc
Collector Current – Pulsed	I _C	1200	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1), T _A = 25°C	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient	D	556	°C/W
Junction-to-Ambient	$R_{\theta JA}$	556	C/VV
Total Device Dissipation Alumina	P_{D}		
Substrate, (Note 2) T _A = 25°C		300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance,			
Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

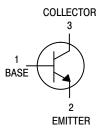


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SOT-23 (TO-236) CASE 318 STYLE 6



MARKING DIAGRAM



EG = Specific Device Code M = Date Code*

= Pb-Free Package

(*Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BCW66GLT1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SBCW66GLT1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
BCW66GLT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BCW66GLT1G, SBCW66GLT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	45	_	_	Vdc
Collector – Emitter Breakdown Voltage (I _C = 10 μAdc, V _{EB} = 0)	V _{(BR)CES}	75	_	_	Vdc
Emitter – Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	5.0	_	-	Vdc
Collector Cutoff Current $(V_{CE} = 45 \text{ Vdc}, I_E = 0)$ $(V_{CE} = 45 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$	ICES	_ _	_ _	20 20	nAdc μAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)	I _{EBO}	-	-	20	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C = 100 \ \mu Adc, \ V_{CE} = 10 \ Vdc) \\ &(I_C = 10 \ mAdc, \ V_{CE} = 1.0 \ Vdc) \\ &(I_C = 100 \ mAdc, \ V_{CE} = 1.0 \ Vdc) \\ &(I_C = 500 \ mAdc, \ V_{CE} = 2.0 \ Vdc) \end{aligned} $	h _{FE}	50 110 160 60	- - -	- - 400 -	-
Collector – Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$) ($I_C = 100 \text{ mAdc}$, $I_B = 10 \text{ mAdc}$)	V _{CE(sat)}	_ _		0.7 0.3	Vdc
Base – Emitter Saturation Voltage (I _C = 500 mAdc, I _B = 50 mAdc)	V _{BE(sat)}	-	_	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain — Bandwidth Product (I _C = 20 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	f _T	100	-	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	-	12	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	-	80	pF
Noise Figure $(V_{CE}=5.0~Vdc,~I_{C}=0.2~mAdc,~R_{S}=1.0~k\Omega,~f=1.0~kHz,~BW=200~Hz)$	NF	-	-	10	dB
SWITCHING CHARACTERISTICS	•	•	-		-
Turn–On Time ($I_{B1} = I_{B2} = 15 \text{ mAdc}$)	t _{on}	_	_	100	ns
Turn–Off Time (I_C = 150 mAdc, R_L = 150 Ω)	t _{off}	_	_	400	ns
	•			•	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

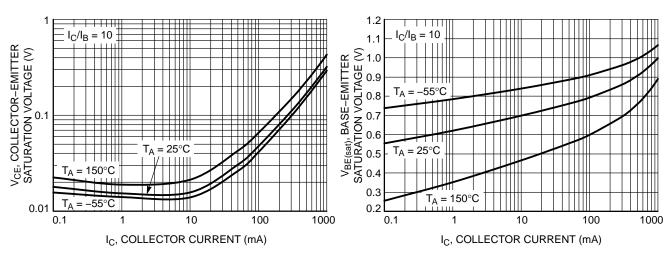


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

Figure 2. Base Emitter Saturation Voltage vs.
Collector Current

BCW66GLT1G, SBCW66GLT1G

TYPICAL CHARACTERISTICS

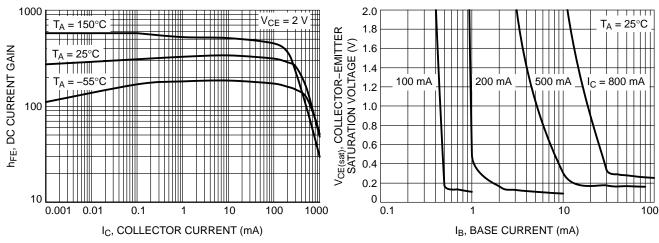


Figure 3. DC Current Gain vs. Collector Current

Figure 4. Saturation Region

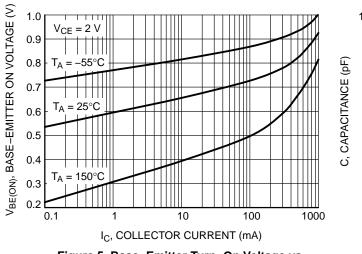


Figure 5. Base–Emitter Turn–On Voltage vs.
Collector Current

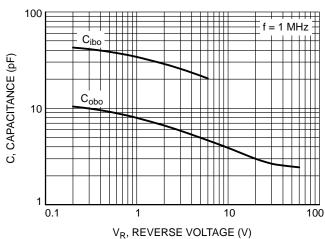


Figure 6. Capacitance

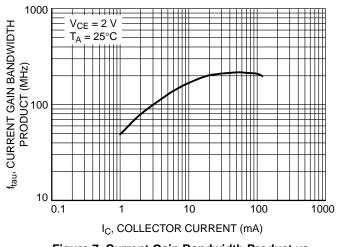


Figure 7. Current Gain Bandwidth Product vs.

Collector Current

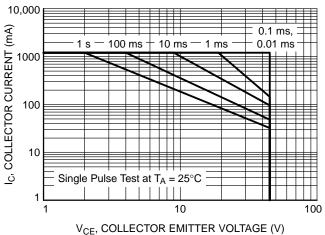


Figure 8. Safe Operating Area

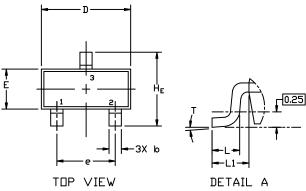




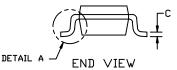
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DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°



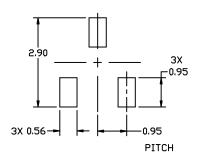


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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